

T10B series Sibod™

FEATURES

- Glass passivated junction
- High current diverting capability, 250A
- Low capacitance, less than 200pF
- UL recognised
- Automatic reset
- Does not degrade

APPLICATION

- Bi-directional device for telephone and line card protection

ELECTRICAL CHARACTERISTICS (Tamb = +25°C)

SYMBOL	PARAMETER
V _{RM}	Stand-off Voltage
V _{BR}	Breakdown Voltage
I _H	Holding Current
V _R	Continuous Reverse Voltage.

ABSOLUTE RATINGS (limiting values) (T_j = + 25°C) L = 10mm

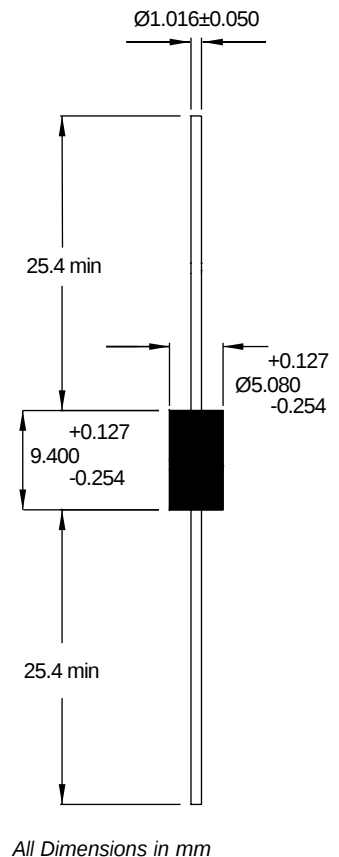
SYMBOL	PARAMETER	VALUE	UNIT
P	Power Dissipation on Infinite Heatsink Tamb = 50°C	5	W
I _{pp}	Peak Pulse Current 10x1000µsec 10/700 1.5KV 8-20 us expo	100 125 250	A
I _{tsm}	Non Repetitive Surge Peak on state Current tp = 20 ms	50	A
di/dt	Critical Rate of Rise of on-state Current Non repetitive	100	A/µS
T _{stg} T _j	Storage and Operating Junction Temperature Range	-40 to 150 150	°C °C
T _l	Maximum Lead Temperature for soldering During 10s at 4mm from Case	230	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	VALUE	UNIT
R _{th(j-i)} R _{th(j-a)}	Junction-leads on Infinite Heatsink Junction-ambient on Printed Circuit L = 10mm	20 75	°C/W °C/W

All parameters are tested using Fet Test™ Model 3600

DEVICE TYPE	I _{RM} @ V _{RM} max		I _r @ V _R max		V _{BO} @ I _{BO} max		I _H min	C typ
	µA	V	µA	V	V	mA	mA	pF
T10B35	2	32	50	35	55	800	150	180
T10B65	2	55	50	65	80	800	150	160
T10B120	2	110	50	120	160	800	150	140
T10B140	2	120	50	140	200	800	150	140
T10B200	2	170	50	200	265	800	150	130
T10B230	2	200	50	230	300	800	150	120
T10B270	2	230	50	270	350	800	150	120



ORDERING INFORMATION

T10B

Voltage

Packaging Option

B = Bulk (500 pcs)

T = Tape and reeled (1500 pcs)